

WHAT IS CLAIMED IS:

1. A process for lapping the second side of a wafer, which is provided at its first with an ultraviolet tape attached thereto, comprising the steps of:

irradiating the ultraviolet tape attached to the first side of the wafer with ultraviolet light;

maintaining a lapping jig, to which the wafer is placed, at a temperature higher than binder's melting temperature but lower than the deformation temperature of the ultraviolet tape;

applying the binder to an upper surface of the lapping jig;

bonding the first side of the wafer to the lapping jig via the binder;

displacing the lapping jig having the wafer bonded thereto on a lapping plate;

lapping the second side of the wafer cause to the wafer to have a predetermined thickness; and

removing the wafer from the lapping jig.

2. The process as set forth in claim 1, in which the step of maintaining the lapping jig at the temperature further comprises the step of placing the lapping jig on a hot plate for a predetermined period of time causing its temperature to be maintained at a temperature higher than the binder's melting

temperature but lower than a deformation temperature of the ultraviolet tape.

3. The process as set forth in claim 1, in which the
5 binder is Aqua wax.

4. The process as set forth in claim 1, in which the temperature of the lapping jig is maintained within a temperature range of about 45°C to 85°C.

10 5. A method for processing a backside of a wafer, comprising the steps of:

attaching an ultraviolet tape to a front side of a wafer;

grinding the backside of the wafer to cause the wafer to

15 have a first thickness;

irradiating the ultraviolet tape attached to the front side of the wafer with ultraviolet light;

lapping the backside of the wafer to cause the wafer to have a second thickness; and

20 removing the ultraviolet tape from the wafer.

6. The method as set forth in claim 5, in which the step of lapping the backside of the wafer further comprises the steps of:

25 bonding the front side of the wafer to an upper surface of

a lapping jig via binder;

displacing the lapping jig having the wafer bonded thereto
on a lapping plate;

lapping the backside of the wafer to cause the wafer to
5 have a second thickness; and
removing the wafer from the lapping jig.

7. The method as set forth in claim 6, in which the step
of bonding the front side of the wafer to the upper surface of
10 the lapping jig further comprises the step of causing the
lapping jig to be maintained at a temperature higher than the
binder's melting temperature but lower than a deformation
temperature of the ultraviolet tape.

15 8. The method as set forth in claim 7, in which the step
of causing the lapping jig to be maintained at a temperature
higher than the binder's melting temperature but lower than a
deformation temperature of the ultraviolet tape further
comprises the step of placing the lapping jig on a hot plate
20 for a predetermined period of time.

9. The method as set forth in claim 7, in which the binder
is Aqua wax.

25 10. The method as set forth in claim 7, in which the

temperature of the lapping jig is maintained within a temperature range of about 45°C to 85°C.

11. A method for processing a backside of a wafer,
5 comprising the steps of:

attaching an ultraviolet tape to a front side of the wafer;

grinding the backside of the wafer to cause the wafer to have a first thickness;

10 irradiating the ultraviolet tape attached to the front side of the wafer with ultraviolet light;

maintaining a lapping jig at a temperature higher than the binder's melting temperature but lower than a deformation temperature of the ultraviolet tape;

15 applying binder to an upper surface of the lapping jig;

bonding the front side of the wafer to the lapping jig via the binder;

displacing the lapping jig having the wafer bonded thereto on a lapping plate;

20 lapping the backside of the wafer to cause the wafer to have a second thickness;

removing the wafer from the lapping jig; and

removing the ultraviolet tape from the wafer.